

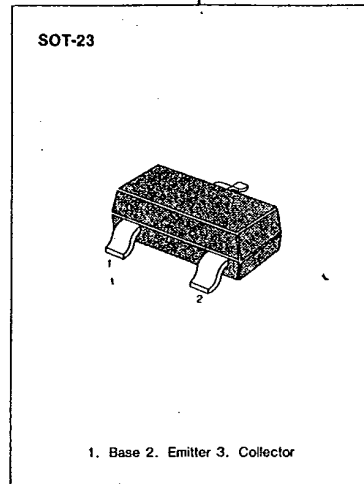
MMBTA13 NPN EPITAXIAL SILICON TRANSISTOR

DARLINGTON AMPLIFIER TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	30	V
Collector-Emitter Voltage	V _{CES}	30	V
Emitter-Base Voltage	V _{EB0}	10	V
Collector Current	I _C	300	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{stg}	150	°C

• Refer to MMBT6427 for graphs



ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Emitter Breakdown Voltage	I _{B CES}	I _C =100μA, I _B =0	30		V
Collector Cutoff Current	I _{CB0}	V _{CB} =30V, I _E =0		100	nA
Emitter Cutoff Current	I _{EB0}	V _{EB} =10V, I _C =0		100	nA
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =10mA	5,000		
		V _{CE} =5V, I _C =100mA	10,000		
Collector-Emitter Saturation Voltage	V _{CE (sat)}	I _C =100mA, I _B =0.1mA		1.5	V
Base-Emitter On Voltage	V _{BE}	I _C =100mA, V _{CE} =5V		2.0	V
Current Gain-Bandwidth Product	f _T	I _C =10mA, V _{CE} =5V f=100MHz	125		MHz

Marking

